

Thermoelectrics Quo Vadis?

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Energy issues

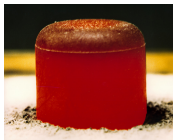
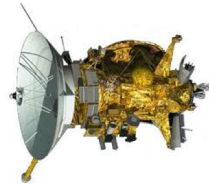
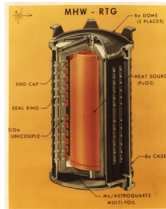
- Huge energy requirements
- CO₂ production, pollution...
- Renewables may cover *growth*
- EU is already reducing consumption
- But need more options...
- Save energy
- Recover waste heat
... with thermoelectrics





Space applications

- Solar flux too small
- Radioactive heat
- Robust energy source
- TEG → Voyager still going
- 5 kg of PuO_2 in Rover





Home applications

- Refrigerator/heater
- TE \rightarrow no moving parts
- (Usually needs a fan)
- Limited efficiency
- Better for integrated apps:
 - On-chip cooling
 - On-board sensors, wifi...
 - and camping!





Big applications?

- Where is the waste heat?
- Auto, aerospace, utilities
- Often $T_{op} \simeq 500\text{ C}$
- Needs: cheap, high volume
- large current, resistant...
- Still huge materials challenge





The game

Why is this talk in this school at all?

Spot surface/interface effects

Interrupt me

Have your name immortalized in pdf



Outline

- 1 TE Concepts
- 2 TE Optimization
- 3 TE Calculations - "how to"



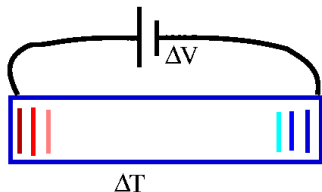
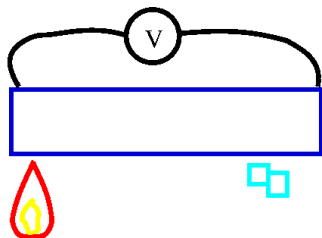
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Peltier Seebeck and Thomson

- Make a thermocouple:
- Seebeck: ΔT produces ΔV
- $S = \Delta V / \Delta T$ (volt / Kelvin)
- Peltier: current produces ΔT
- Thomson(Kelvin):
- 2 effects are reciprocal
- Define single material S

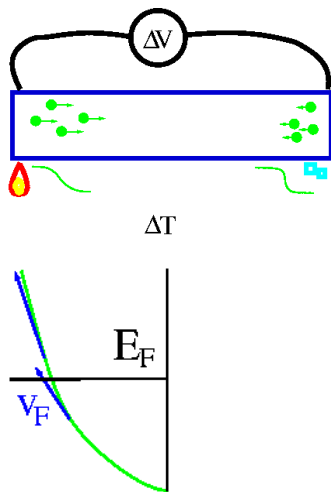




Microscopic view

- Hot side carriers diffuse (e^- , h^+)
- + equilibration mechanism
- m.f.p. or *relaxation time* τ
- microscopic: hom. Bloch solid
- mesoscopic: $T(r)$ or $V(r)$
- Need variation in DOS and v_F

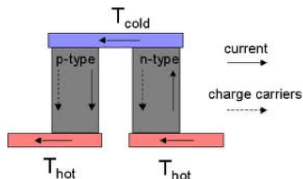
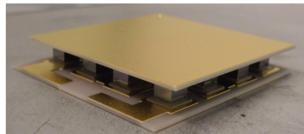
Electron gas: $n(\epsilon) \sim \sqrt{\epsilon}$ & $v_F \sim \sqrt{\epsilon}$
 Above E_F more e^- diffuse \rightarrow n type





TE Devices

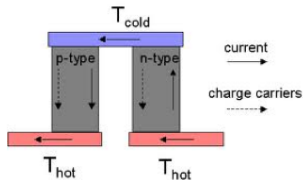
- Seebeck → power generation
- Peltier → heat/cool generation
- couple p and n materials
- thermally in parallel (κ)
- electrically in series (σ)





Device constraints

- Need compatible n and p materials
- Need to match them:
 - chemically
 - charge/thermal fluxes,
 - metal junction, contacts
- Minimize thermal losses
- Maximize contact transparency





Efficiency

What do you want?

- Uses → Different efficiency
- Maximize power?
- Maximize current, heat flux?
- Figure(s) of Merit
- Coeff of Performance

Phonon Glass Electron Crystal
Slack Solid State Phys **34** 1 1979

$$P = \sigma S^2$$

$$z = \frac{\sigma S^2}{\kappa}$$

$$Z_{dev} = \frac{(S_p - S_n)^2}{(\sqrt{\kappa_p/\sigma_p} + \sqrt{\kappa_n/\sigma_n})^2}$$

$$COP = \frac{\gamma T_c - T_h}{(T_c - T_h)(1 + \gamma)}$$

$$\gamma = \sqrt{1 + zT}$$



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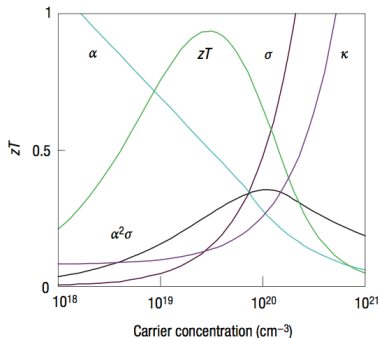
Orders of magnitude

- $10^{-16} < \sigma < 10^9 \Omega^{-1} m^{-1}$
- $0 < |S| < 100s - 1000s$ of $\mu V / K$
- $0.05 < \kappa < 1000s$ W / m / K
- metals: σ κ high, S small
- insulators: κ often high, $\sigma = S = 0$
- ✓ doped dirty semiconductors



Trends in T and μ

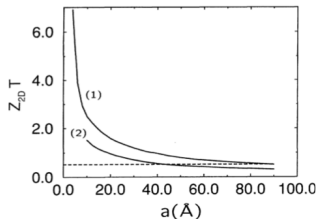
- T increases phonons
- $\sigma, \kappa \searrow$
- $S \nearrow$
- μ increases $N(E_F)$
- $\sigma, \kappa \nearrow$
- $S \searrow$
- Historically: doping + disorder





Novel attempts

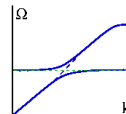
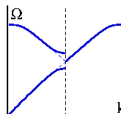
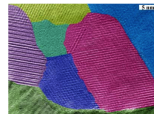
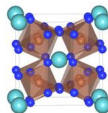
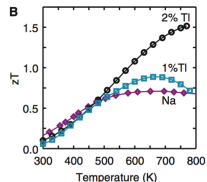
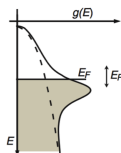
- Hicks and Dresselhaus
Phys. Rev. B **47** 12727 (1993)
- zT vs QWell width a
- μ tuned by doping and a
- Boost: bands + phonon scattering
- Free e^- ... usually wrong
PRB **86** 195301 (2012)
- Few demonstrations of HD scaling
but hugely inspirational





Novel attempts

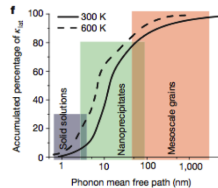
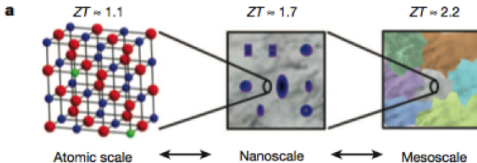
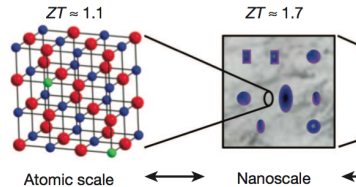
- Localized states
Mahan PNAS **93** 7436 (1996)
Heremans Science **321** 554 (2008)
- Rattlers, skutterudites, disorder...
- Nano alloying (e.g. MIT BiSbTe)
- LAST and related compounds





Novel attempts

- Biswas Nature **489** 414 (2012)
- Atomic doping Na
- Nanocluster doping
- Ball milling of grains
- Kill successive phonon wavelengths





Recap

- Most optimization on phonons and κ
- Doping and T have opposite effects
- S most difficult to control
- Devil is in the details:
 - defects, doping sites
 - band structure effects
 - thermal effects



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Need list

- Transport coefficients
- Functions of T and μ
- σ from electrons
- κ_L from phonons
- S from both
- + *many* scattering mechanisms:
(charged) impurities, defects, *phonons*, boundaries, isotopes...



"Master" equations

Beyond simple models e.g. Slack $\kappa_L \simeq \bar{M}\theta_D^3(VN)^{1/3}/\gamma^2 T$

Broadly 3 ab initio approaches:

- Boltzmann equations

Ziman *Electrons and Phonons* (1960)

- Green-Kubo relations (+MD)

Green JPC **22** 398 (1954); Kubo JPS Japan **12** 570(1957)

- NEGF (too new for comfort)

Jauho J. Phys.: Conf. Ser. **220** 012010 (2010)

Wang Eur. Phys. J. B **62** 381 (2008)

Sergueev Phys Rev B **83** 195415 (2011)



Boltzmann

- Classical stat mech "Hydrodynamic" approach

$$\frac{\partial f_{nk}}{\partial T} - eE \cdot \nabla_k f_{nk} + v_k \cdot \nabla_r f_{nk} = \left. \frac{\partial f_{nk}}{\partial t} \right|_{coll}$$

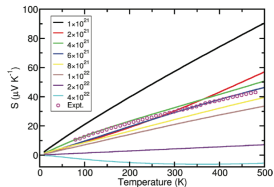
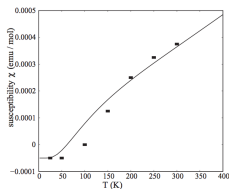
- Semi-classical: f_{FD} , N_{BE} , matrix elements in $\partial f / \partial t|_{coll}$
- Analogous equation for phonons
- Beyond lin resp \rightarrow Monte Carlo solutions
- Relaxation time: $\partial f|_{coll} = \delta f / \tau_k$

$$\frac{1}{\tau} = \frac{1}{\tau_{imp}} + \frac{1}{\tau_{ph}} + \frac{1}{\tau_{iso}} + \frac{1}{\tau_{bdy}} \dots$$



Relaxation Time

- Constant relaxation time $\tau_k(T) = \tau$
BoltzTrap Madsen CPC **175** 67 (2006)
BoltzWann Pizzi arXiv:1305.1587
- ϵ_{nk} on dense k-point grid
- Gives $\sigma_{\alpha\beta}(\epsilon)$, S , σ , $\kappa_{el}(\mu, T)$
- Many DFT codes interface bands with BT and Wannier90/BW
- "Out of the box" but parameter τ
- We can do better...

OsSi Xu PRB **87** 134302 (2013)FeSb₂ Diakhate PRB **84** 125210 (2011)



Elastic Variational

- Variational Approximation (lin resp) PB Allen PRB **17** 3725 (1978)

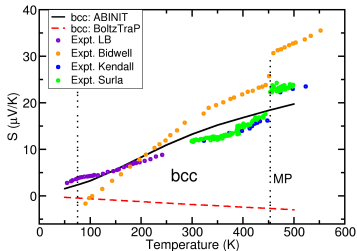
$$\rho \sim \frac{1}{\langle \mathcal{T} \rangle} \sim \int (v_k - v_{k'})^2 |g_{kk'}|^2 f(\epsilon_k) [1 - f(\epsilon_{k'})] \\ \times \{ [N(\Omega) + 1] \delta(\epsilon_k - \epsilon_{k'} - \Omega) + N(\Omega) \delta(\epsilon_k - \epsilon_{k'} + \Omega) \}$$

- (Elastic) Lowest Order VA: $\epsilon_k = \epsilon_{k'} = E_F$
- Much more work: phonons and integrations
- Phonons: *abinit*, QE, vasp, anything+phonopy
- In elastic LOVA $S = 0!$

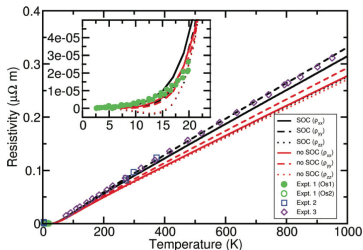


Inelastic Variational

- Full inelastic treatment needed
- Allen decouples ϵ and k integrations
- For Li sign changes wrt RTA
- Limits: steady state, linear, not fully quantum



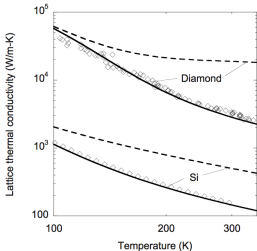
Lithium: Xu, Verstraete unpublished

Osmium: Xu PRB **87** 134302 (2013)

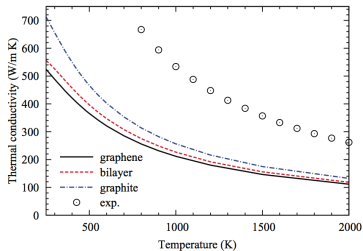


Phonon Variational

- Variational phonon κ_L
- 3-phonon anharmonic scattering
- Energy conservation $\delta(\Omega_3 - \Omega_1 \pm \Omega_2)$
- DFPT Mingo PRB 84, 125426 (2011)



PRB 80 125203 (2009)

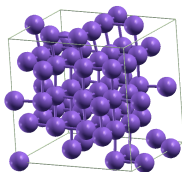
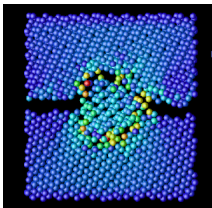


PRB 87, 214303 (2013)



Green-Kubo

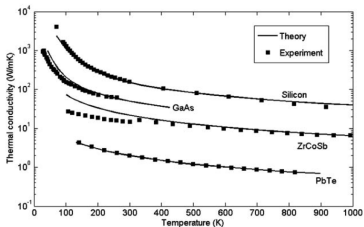
- $j = \langle j \rangle + \Delta j$ (heat or charge)
- Universal Onsager-type relations: $\sigma \sim \int \langle j(0)j(t) \rangle dt$
- Charge current, classical heat current ok
- Molecular Dynamics: $v_{at}(t) \rightarrow j_Q(t) \rightarrow \kappa$
- Quantum heat = challenge: need energy density
- Trajectories from MD, TB, DFT...



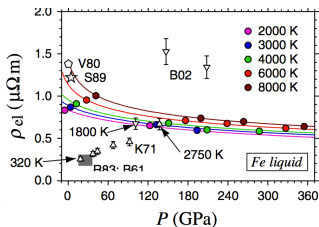


Green-Kubo

- Easy: many classical potential codes do this (GULP, LAMMPS...) + some TB and DFT codes
- Size effects: maximum λ , T_{max}
- Ergodicity issues
- Often fit a functional form to "safe" region in T or t



Zebarjadi En Env Sci (2011)

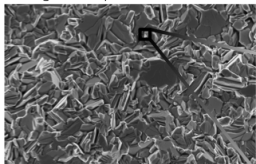


de Koker PNAS **190** 4070 (2012)



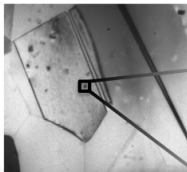
Multiscale needs

Macro (SEM image. Shades correspond to surface orientations, unrelated to grains. At this scale the material is homogeneous.)



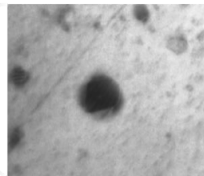
— 3 μm

Meso (TEM image showing grain boundaries and embedded nanoparticles. Transport at this scale is described by the BTE.)



— 200 nm

Micro (TEM image of an embedded nanoparticle. Scattering at this scale requires an atomistic description.)



— 10 nm

Fig 1: Bi₂Te₃ with embedded nanoparticles
(images by G. Bernard-Granger, CEA-Grenoble -Acta Materialia, 2012.-)



Multiscale todo list

- Atomistic → meso BTE → FE methods → device equation
- Which information to pass, how much, and how?
- Transport coefficients: anisotropic, T and μ dependent
- Add intermediate level grain/dopant/interface
Empirical potentials? TB? Assemble DFT pieces?



Conclusions

- Most TE coefficients accessible from DFT
- System size, complexity are the problem
- Defects, explicit dopants only beginning to be treated
- Did I mention complex electronic structure?
- Intrinsically multiscale problem/solution



Acknowledgements

Ideas++

- Natalio Mingo
- Georg Madsen
- Nicola Marzari
- Bin Xu

Your name in lights



Preliminary list

Surface/interface effects

almost all neglected at present at ab initio level

- Contacts
- Grains, cluster doping, 2D defects
- Spontaneous nanoalloying
- Heterostructures
- Sample surface (+roughness)
- Interdiffusion of defects, impurities...